Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

NTD4909N

Power MOSFET
30 V, 41 A, Single N–Channel, DPAK/IPAK

Features
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb–Free Devices

Applications
- CPU Power Delivery
- DC–DC Converters

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain–to–Source Voltage			V_{DSS}	30	V
Gate–to–Source Voltage			V_{GS}	±20	V
Continuous Drain Current ($R_{\theta JA}$) (Note 1)	Steady State	T_A = 25°C	I_D	12.1	A
		T_A = 100°C		8.6	
Power Dissipation ($R_{\theta JA}$) (Note 1)		T_A = 25°C	P_D	2.6	W
Continuous Drain Current ($R_{\theta JA}$) (Note 2)		T_A = 25°C	I_D	8.8	A
		T_A = 100°C		6.2	
Power Dissipation ($R_{\theta JA}$) (Note 2)		T_A = 25°C	P_D	1.37	W
Continuous Drain Current ($R_{\theta JC}$) (Note 1)		T_C = 25°C	I_D	41	A
		T_C = 100°C		29	
Power Dissipation ($R_{\theta JC}$) (Note 1)		T_C = 25°C	P_D	29.4	W
Pulsed Drain Current	t_p=10μs	T_A = 25°C	I_{DM}	167	A
Current Limited by Package		T_A = 25°C	$I_{DmaxPkg}$	60	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 175	°C
Source Current (Body Diode)			I_S	27	A
Drain to Source dV/dt			dV/dt	7.0	V/ns
Single Pulse Drain–to–Source Avalanche Energy (T_J = 25°C, V_{DD} = 50 V, V_{GS} = 10 V, L = 0.1 mH, $I_{L(pk)}$ = 24 A, R_G = 25 Ω)			E_{AS}	28	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface–mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
2. Surface–mounted on FR4 board using the minimum recommended pad size.

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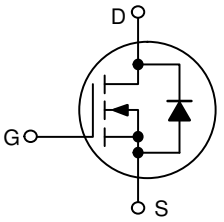
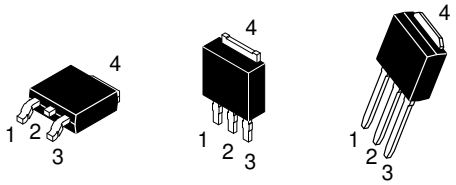
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	8.0 mΩ @ 10 V	41 A
	12 mΩ @ 4.5 V	



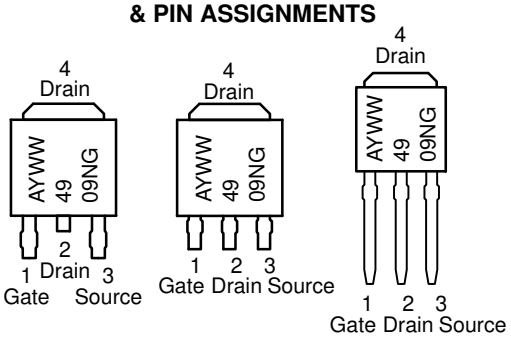


CASE 369AA DPAK (Bent Lead) STYLE 2

CASE 369AD IPAK (Straight Lead)

CASE 369D IPAK (Straight Lead DPAK)

MARKING DIAGRAMS & PIN ASSIGNMENTS



A = Assembly Location
Y = Year
WW = Work Week
4909N = Device Code
G = Pb–Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	5.1	°C/W
Junction−to−TAB (Drain)	$R_{\theta JC-TAB}$	4.3	
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	58.2	
Junction−to−Ambient − Steady State (Note 4)	$R_{\theta JA}$	110	

3. Surface−mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
4. Surface−mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.0	1.7	2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				4.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A		6.5	8.0	mΩ
			I_D = 15 A		6.5		
		V_{GS} = 4.5 V	I_D = 30 A		9.5	12	
			I_D = 15 A		9.5		
Forward Transconductance	gFS	V_{DS} = 1.5 V, I_D = 30 A			52		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 15 V			1314		pF
Output Capacitance	C_{oss}				487		
Reverse Transfer Capacitance	C_{rss}				17.4		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 30 A			7.6		nC
Threshold Gate Charge	$Q_{G(TH)}$				2.1		
Gate−to−Source Charge	Q_{GS}				4.3		
Gate−to−Drain Charge	Q_{GD}				1.3		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 30 A			17.5		nC
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			11		ns
Rise Time	t_r				21		
Turn−Off Delay Time	$t_{d(off)}$				17		
Fall Time	t_f				2.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.
7. Assume terminal length of 110 mils.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			8.0		ns
Rise Time	t_r				19		
Turn−Off Delay Time	$t_{d(off)}$				21		
Fall Time	t_f				2.3		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 30 A	T_J = 25°C		0.9	1.1	V
			T_J = 125°C		0.8		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 30 A			30		ns
Charge Time	ta				16		
Discharge Time	tb				14		
Reverse Recovery Time	Q_{RR}				20		nC
PACKAGE PARASITIC VALUES							
Source Inductance (Note 7)	L_S	T_A = 25°C			2.99		nH
Drain Inductance, DPAK	L_D				0.0164		
Drain Inductance, IPAK (Note 7)	L_D				1.88		
Gate Inductance (Note 7)	L_G				4.9		
Gate Resistance	R_G				1.0	2.0	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.
7. Assume terminal length of 110 mils.

ORDERING INFORMATION

Order Number	Package	Shipping†
NTD4909NT4G	DPAK (Pb−Free)	2500 / Tape & Reel
NTD4909N−1G	IPAK (Pb−Free)	75 Units / Rail
NTD4909N−35G	IPAK Trimmed Lead (Pb−Free)	75 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

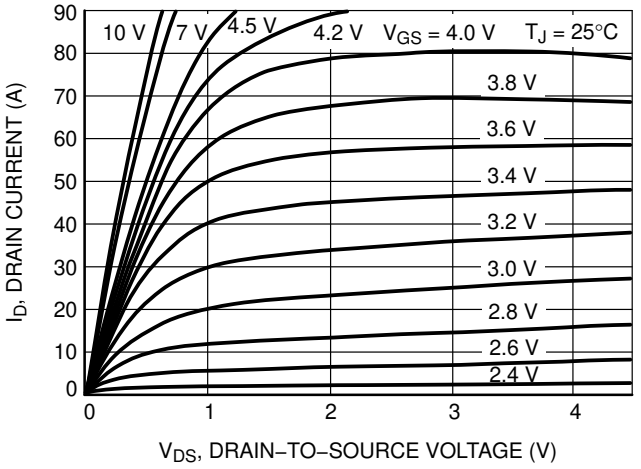


Figure 1. On−Region Characteristics

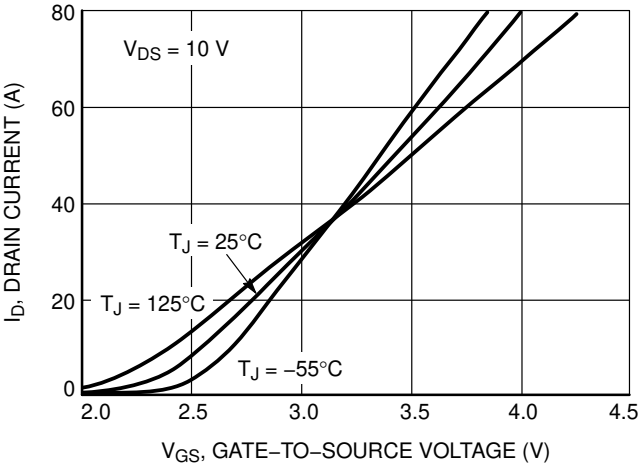


Figure 2. Transfer Characteristics

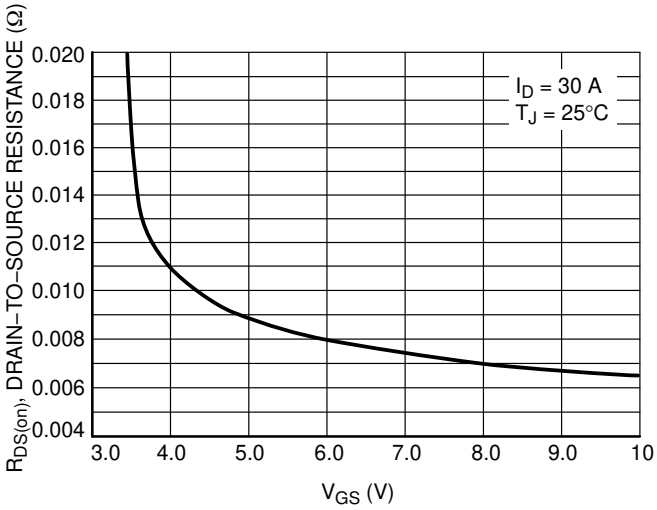


Figure 3. On−Resistance vs. V_{GS}

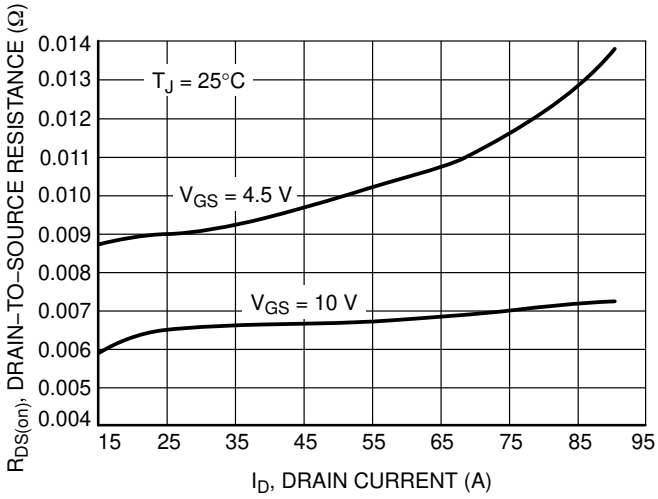


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

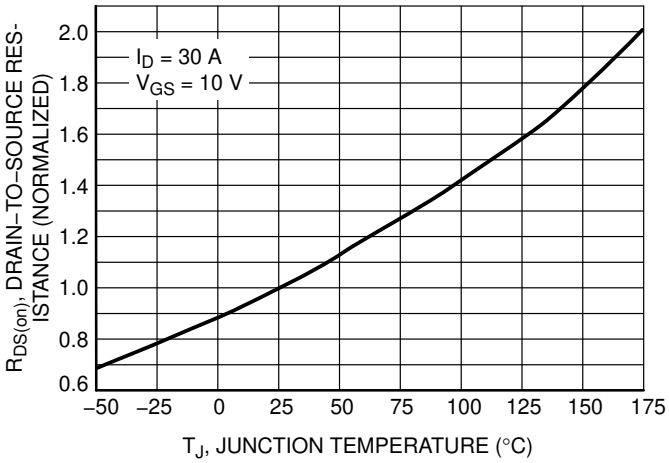


Figure 5. On−Resistance Variation with Temperature

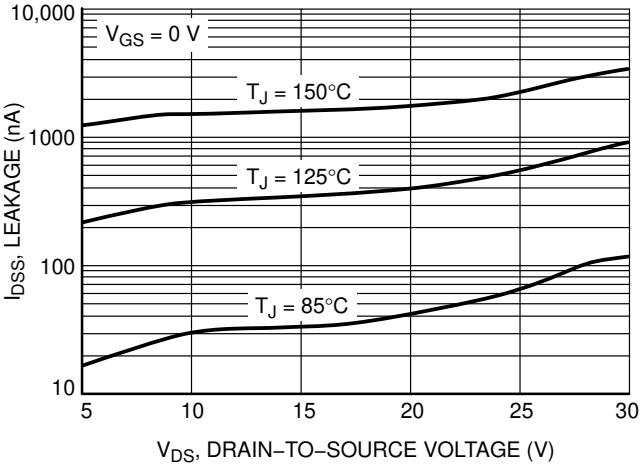


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

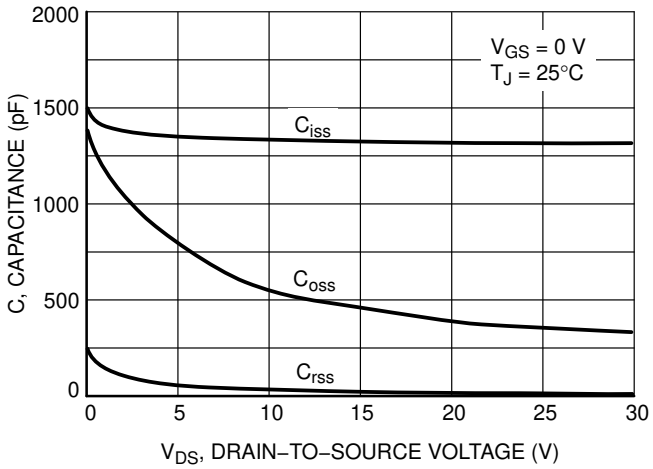


Figure 7. Capacitance Variation

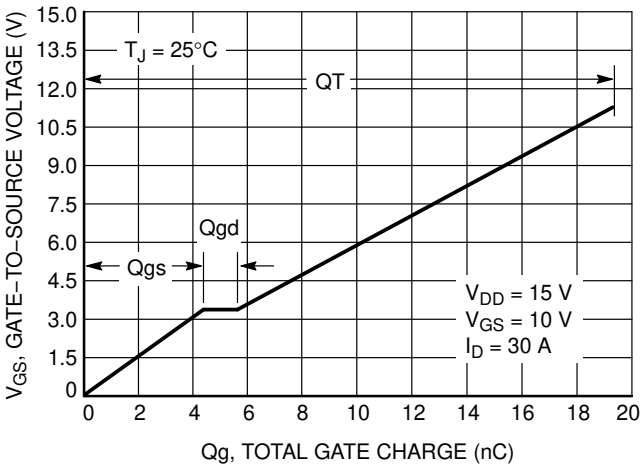


Figure 8. Gate–to–Source and Drain–to–Source Voltage vs. Total Charge

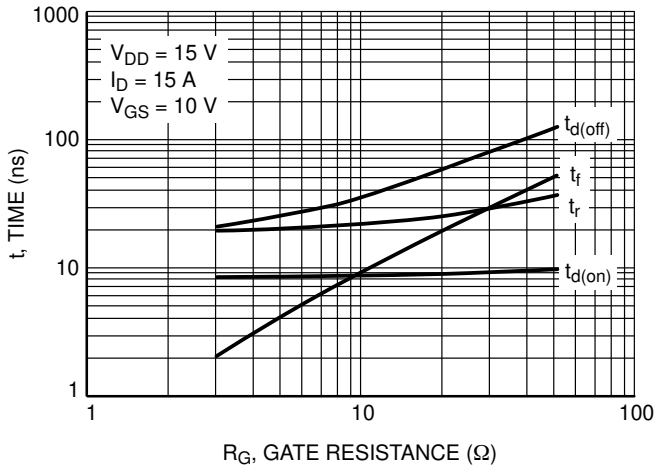


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

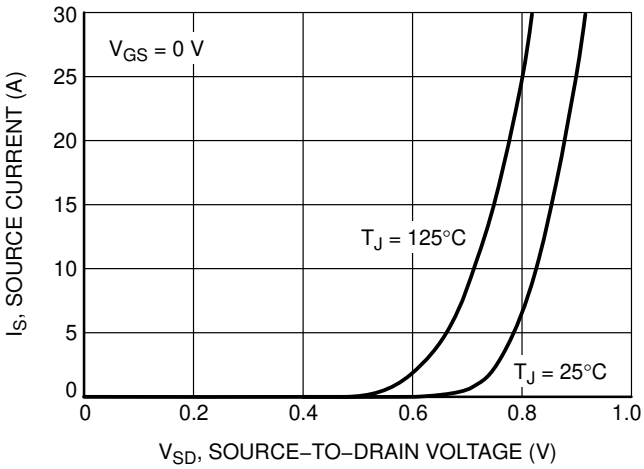


Figure 10. Diode Forward Voltage vs. Current

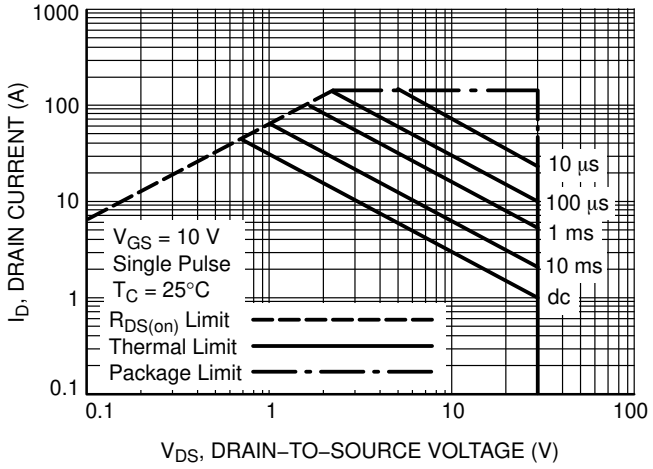


Figure 11. Maximum Rated Forward Biased Safe Operating Area

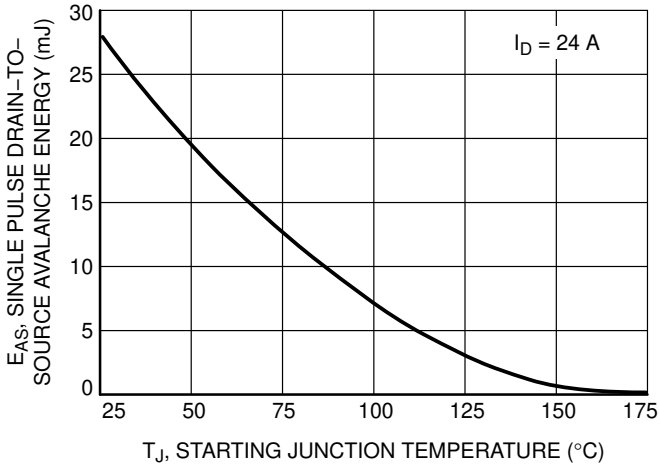


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL CHARACTERISTICS

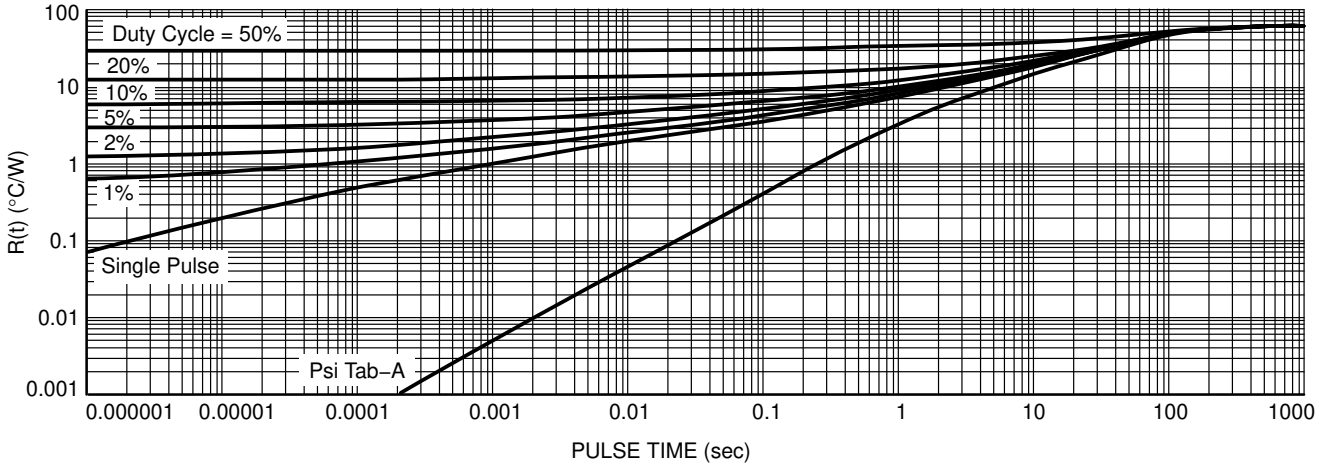


Figure 13. FET Thermal Response

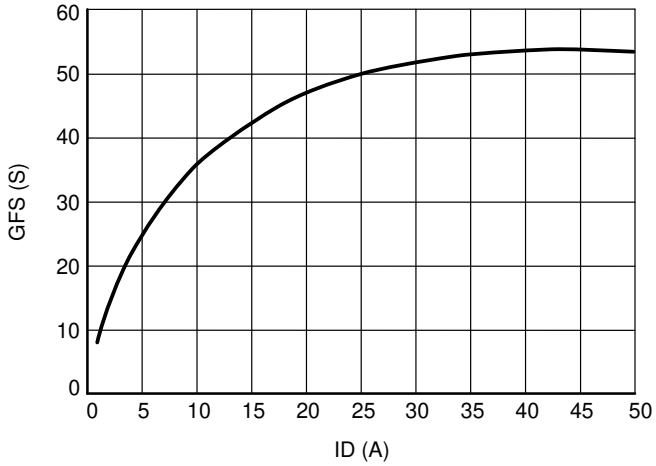
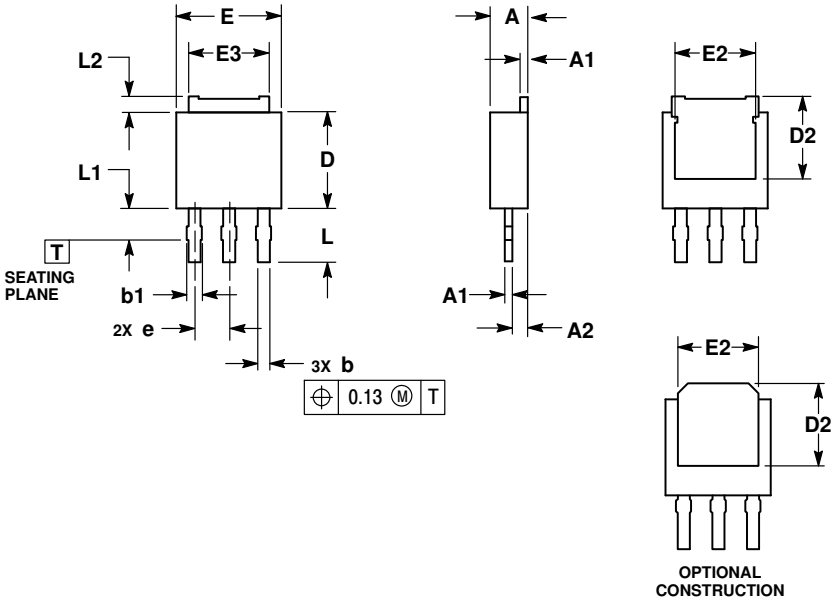


Figure 14. GFS vs. ID

PACKAGE DIMENSIONS

3.5 MM IPAK, STRAIGHT LEAD
CASE 369AD
ISSUE B

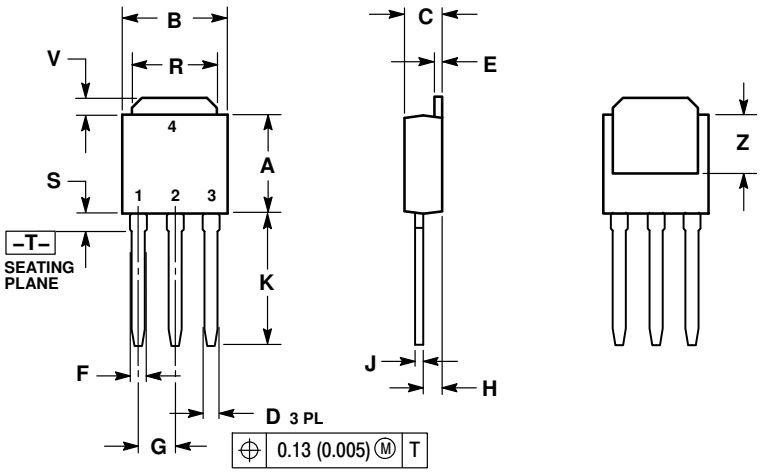


NOTES:
1.. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2.. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL TIP.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD GATE OR MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
A	2.19	2.38
A1	0.46	0.60
A2	0.87	1.10
b	0.69	0.89
b1	0.77	1.10
D	5.97	6.22
D2	4.80	---
E	6.35	6.73
E2	4.57	5.45
E3	4.45	5.46
e	2.28 BSC	
L	3.40	3.60
L1	---	2.10
L2	0.89	1.27

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

IPAK
CASE 369D
ISSUE C



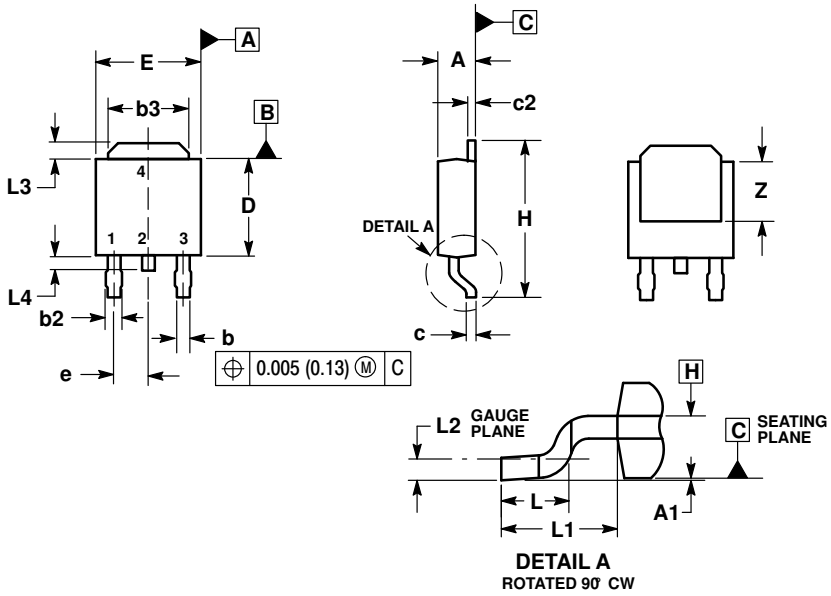
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

PACKAGE DIMENSIONS

DPAK (SINGLE GUAGE)
CASE 369AA
ISSUE B

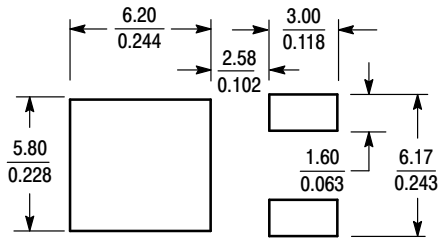


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

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